

**FX203**

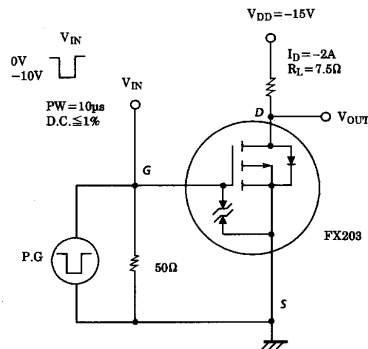
P-Channel Silicon MOSFET

Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.

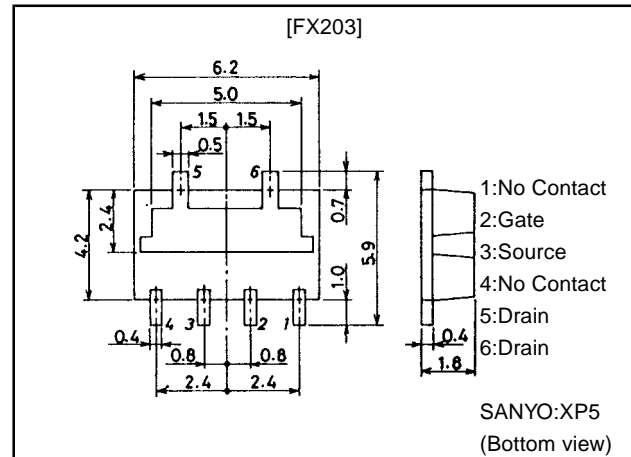
Switching Time Test Circuit



Package Dimensions

unit:mm

2121



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-30	V
Gate-to-Source Voltage	V_{GS}		±20	V
Drain Current (DC)	I_D		-4	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-16	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	8	W
	P_D	Mounted on ceramic board (750mm ² × 0.8mm)	2	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA$, $V_{GS} = 0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V$, $V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V$, $V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V$, $I_D = -1mA$	-1.0		-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V$, $I_D = -2A$	1.5	3		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -2A$, $V_{GS} = -10V$		120	160	mΩ
	$R_{DS(on)}$	$I_D = -2A$, $V_{GS} = -4V$		210	290	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -10V$, $f = 1MHz$		370		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V$, $f = 1MHz$		230		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10V$, $f = 1MHz$		70		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	t_r	See specified Test Circuit		50		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		135		ns
Fall Time	t_f	See specified Test Circuit		125		ns
Diode Forward Voltage	V_{SD}	$I_S = -4A$, $V_{GS} = 0$		-1.0	-1.2	V

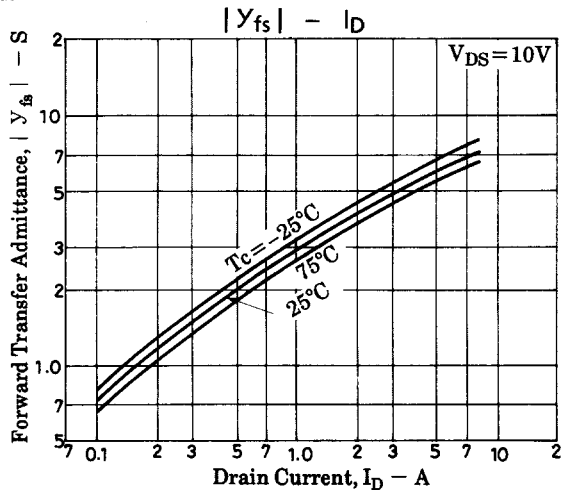
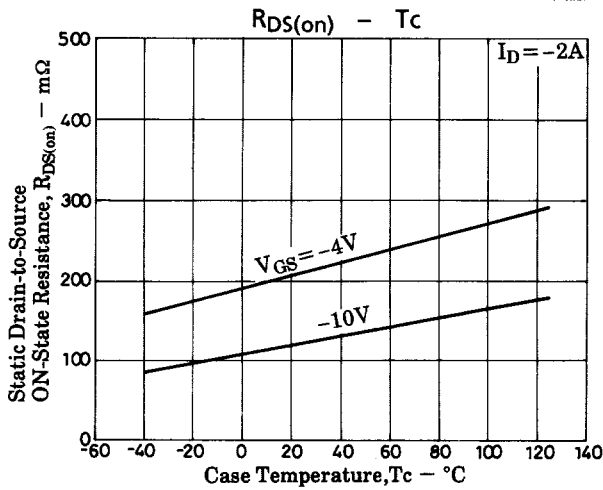
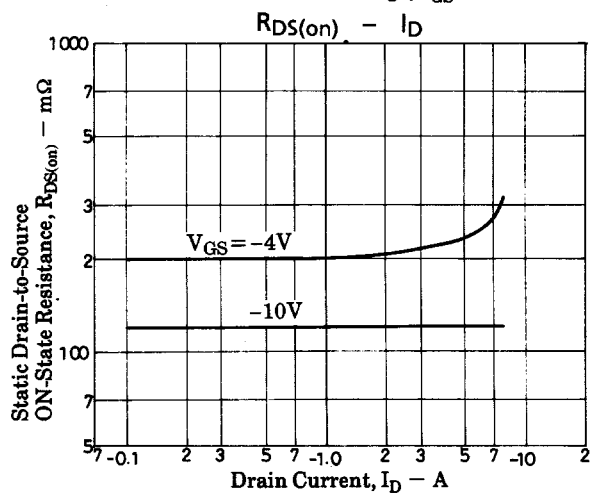
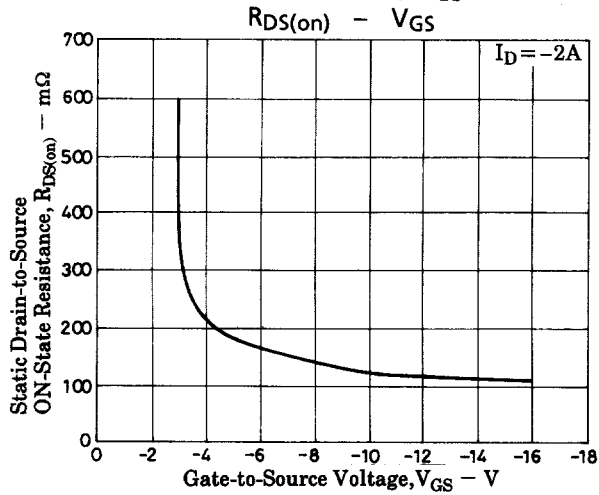
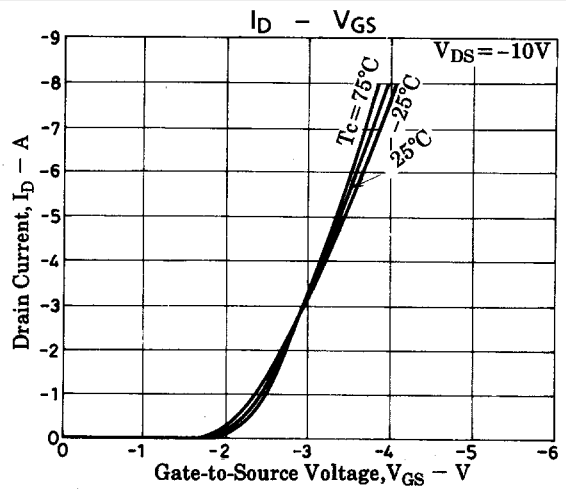
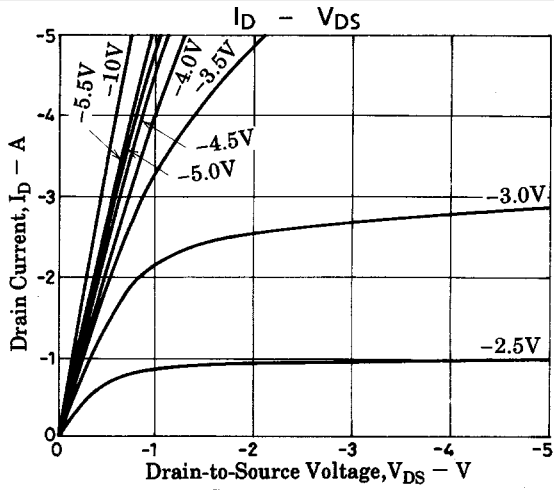
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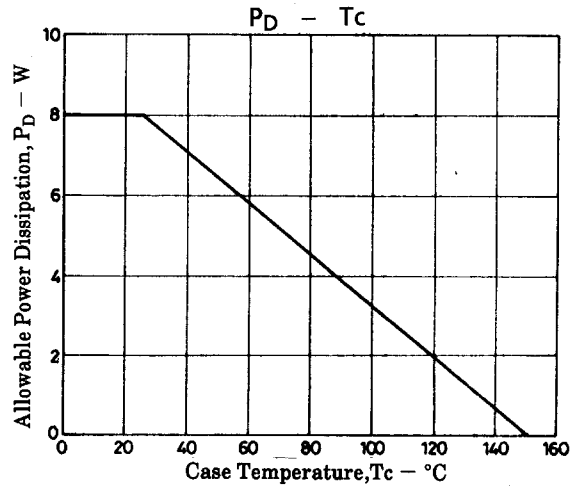
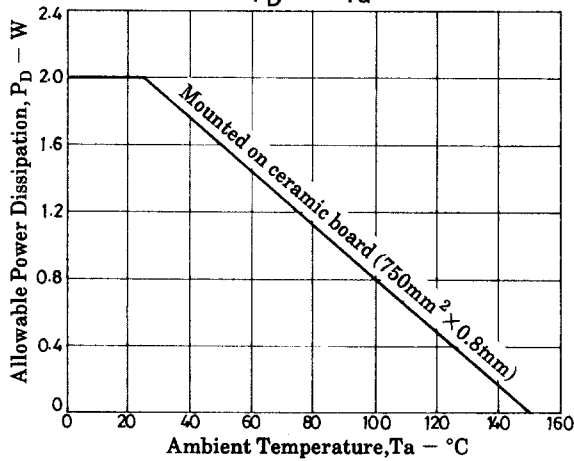
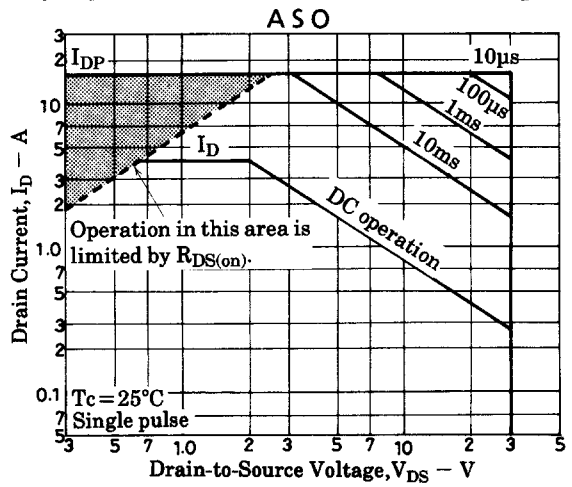
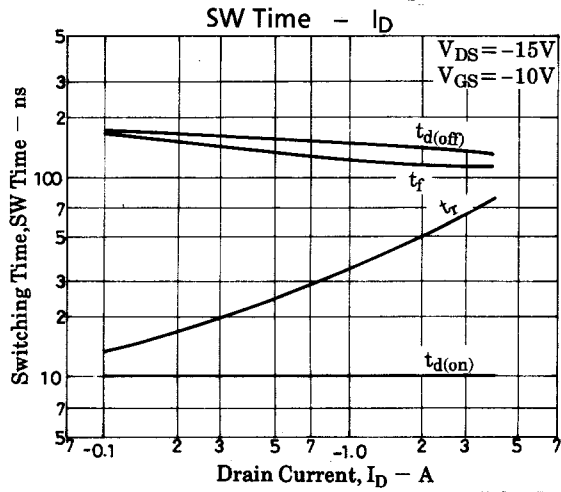
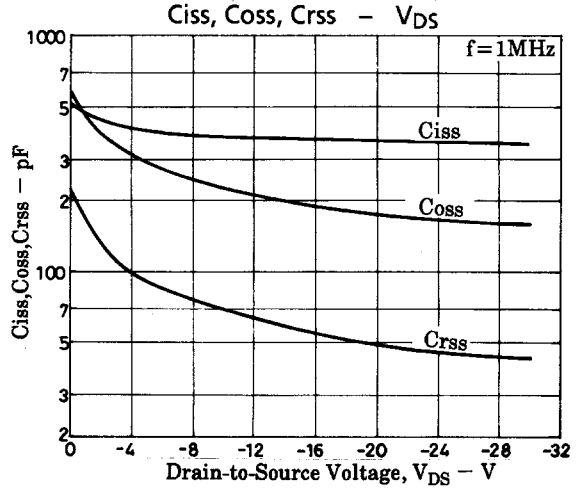
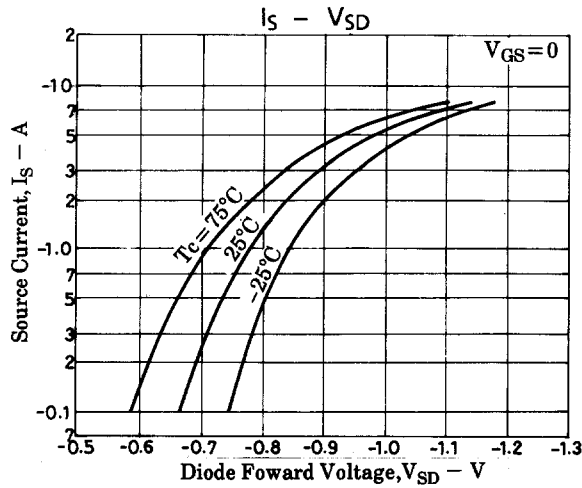
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